In the Claims:

Please cancel claims 2, 4-5 and 13-20 without prejudice or disclaimer.

Please amend claims 1, 3 and 7, as follows:

Claim 1 (currently amended) An additive of following Formula 1 Formulas 3-7 for a photoresist composition for a resist flow process:

Formula 1



wherein, A is H or OR",

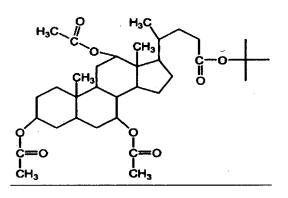
B is H or OR", and

R, R', R'' and R''' are independently selected from the group consisting of C_1 - C_{10} alkyl, C_1 - C_{10} alkylearbonyl, and C_1 - C_{10} alkylearbonyl group (OH).

Formula 3

Formula_5

Formula 6

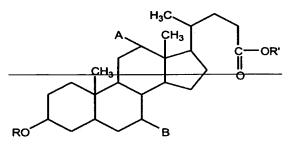


Formula 7 H₃C CH₃ CH₃

Claim 2 (currently canceled)

Claim 3 (currently amended) A photoresist composition comprising:
a photoresist polymer, a photoacid generator, an additive of following Formula
4 Formulas 3-7, and an organic solvent,

Formula 1



wherein, A is H or OR",

B is H or OR", and

R, R', R'' and R''' are independently selected from the group consisting of C_1 - C_{10} alkyl, C_1 - C_{10} alkoxyalkyl, C_1 - C_{10} alkylearbonyl, and C_1 - C_{10} alkylearbonyl containing at least one hydroxyl group (-OH).

Formula 3

Formula 4

Formula 5

Formula 6



Formula 7 H₃C C CH₃ CH

Claims 4-5 (currently canceled)

Claim 6 (original) The photoresist composition of claim 3 wherein the photoresist polymer is a compound of following Formulas 8 or 9:

Formula 8

Formula 9

wherein, R₁ is and acid labile protecting group;

R₂ is hydrogen;

 R_3 is hydrogen, selected from the group consisting of C_1 - C_{10} alkyl, C_1 - C_{10} alkoxyalkyl, and C_1 - C_{10} alkyl containing at least one hydroxyl group (-OH);

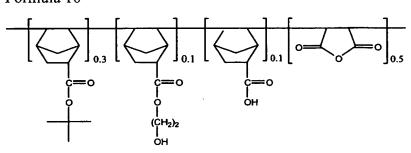
n is an integer from 1 to 5; and

w, x, y and z individually denote the mole ratio of each monomer, preferably with proviso that w + x + y = 50mol%, and z is 50mol%.

Claim 7 (currently amended) The photoresist composition of claim 6 wherein the photoresist polymer is selected from the group consisting of compounds of following Formulas 10 to 13:

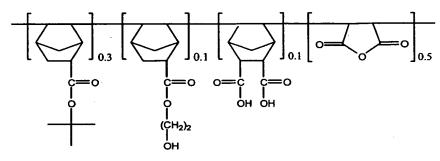
Formula 10





Formula 11

Formula 12



Formula 13

Claim 8 (original) The photoresist composition of claim 3 wherein the additive is present in an amount ranging from about 1 to about 70% by weight of the photoresist polymer.

Claim 9 (original) The photoresist composition of claim 3 wherein said photoacid generator is selected from the group consisting of diphenyl iodide hexafluorophosphate, diphenyl iodide hexafluoroarsenate, diphenyl iodide hexafluoroantimonate, diphenyl p-methoxyphenyl triflate, diphenyl p-toluenyl triflate, diphenyl p-isobutylphenyl triflate, diphenyl p-tert-butylphenyl triflate, triphenylsulfonium hexafluororphosphate, triphenylsulfonium hexafluoroarsenate,

triphenylsulfonium hexafluoroantimonate, triphenylsulfonium triflate, dibutylnaphthylsulfonium triflate, and mixtures thereof.

Claim 10 (original) The photoresist composition of claim 3 wherein the photoacid generator is present in an amount ranging from about 0.01 to about 10% by weight of the photoresist polymer.

Claim 11 (original) The photoresist composition of claim 3 wherein the organic solvent is selected from the group consisting of propyleneglycol methyl ether acetate, ethyl lactate, methyl 3-methoxypropionate, ethyl 3-ethoxypropionate and cyclohexanone.

Claim 12 (original) The photoresist composition of claim 3 wherein the organic solvent is present in a range of from about 100 % to about 1000% by weight of the photoresist polymer.

Claims 13-20 (currently canceled)